PNZ327 (PN327)

Silicon planar type

For optical control systems

■ Features

- Fast response which is well suited to high speed modulated light detection: t_r , $t_f = 50$ ns (typ.)
- High sensitivity, high reliability
- Peak emission wavelength matched with infrared light emitting diodes: $\lambda_p = 900 \text{ nm}$ (typ.)
- Wide detection area, wide half-power angle: $\theta = 70^{\circ}$ (typ.)

■ Absolute Maximum Ratings $T_a = 25$ °C

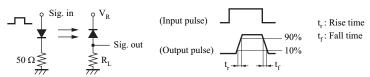
Parameter	Symbol	Rating	Unit	
Reverse voltage	V _R	30	V	
Power dissipation	P_{D}	100	mW	
Operating ambient temperature	T _{opr}	-30 to +85	°C	
Storage temperature	T _{stg}	-40 to +100	°C	

■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Sensitivity to infrared radiation *1	S_{IR}	$V_R = 5 \text{ V}, H = 0.1 \text{ mW/cm}^2$	4.5		ijo).	μΑ
Photocurrent *2	$I_{\rm L}$	$V_R = 10 \text{ V}, L = 1000 \text{ lx}$	SO	70	Vo	μΑ
Drain current	I_{D}	$V_R = 10 \text{ V}$		5	50	nA
Terminal capacitance	C _t	$V_R = 0 V, f = 1 MHz$	8 18	70	3,	pF
Peak sensitivity wavelength	$\lambda_{ ext{PD}}$	$V_R = 10 \text{ V}$	1/1/0	900		nm
Half-power angle	θ	The angle when sensitivity to infrared radiation is halved	0,020	70		0
Rise time *3	t _r	V 10VP 110	50	50		ns
Fall time *3	$t_{\rm f}$	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega$		50		ns
Rise time *3	t _r	V 10 V D 10010		5		μs
Fall time *3	$t_{\rm f}$	$V_R = 10 \text{ V}, R_L = 100 \text{ k}\Omega$		5		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

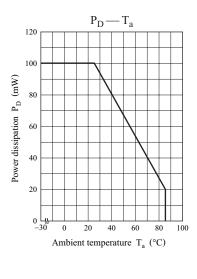
- 2. Spectral sensitivity characteristics: Sensitivity for wave length over 400 nm maximum sensitivity ratio is 100%.
- 3. This device is designed by disregarding radiation.
- 4. *1:Source: Infrared emitters ($\lambda = 940 \text{ nm}$)
 - *2:Source: Tungsten lamp (color temperature 2 856K)
 - *3: Switching time measurement circuit

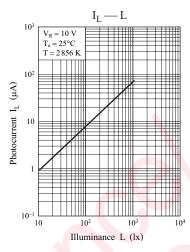


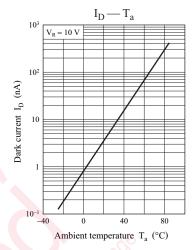
Note) The part number in the parenthesis shows conventional part number.

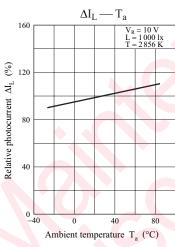
PNZ327

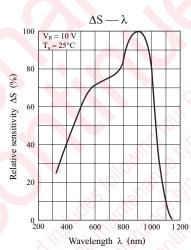
Panasonic

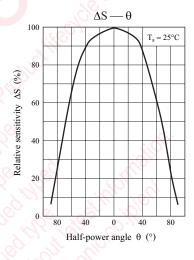


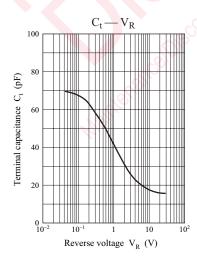


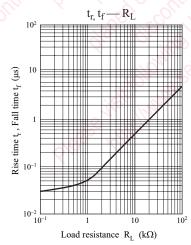


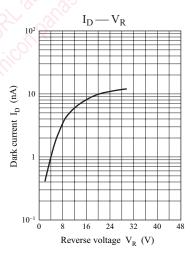










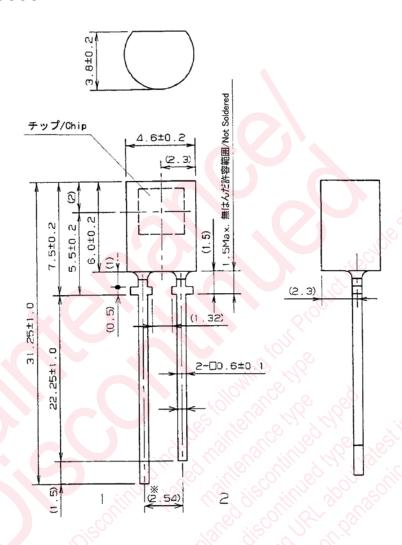


2 SHE00038DED

Panasonic PNZ327

■ Package (Unit: mm)

LPXFSN2S0001



- Pin name
 - 1: Anode
 - 2: Cathode

SHE00038DED 3

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